

EB52F3A15N-25.000M



ITEM DESCRIPTION

Temperature Compensated Quartz Crystal Clock Oscillators TCXO LVCMOS (CMOS) 3.3Vdc 14-Pin DIP Metal Thru-Hole 25.000MHz ± 1.5 ppm Maximum 0°C to +50°C

ELECTRICAL SPECIFICATIONS

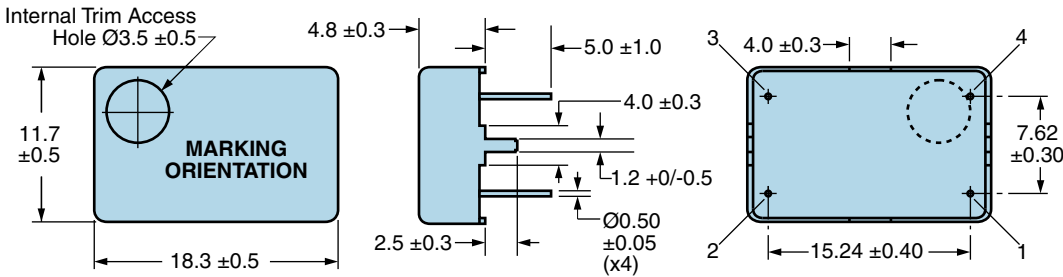
Nominal Frequency	25.000MHz
Frequency Stability	± 1.5 ppm Maximum (Inclusive of Operating Temperature Range)
Frequency Stability vs. Input Voltage	± 0.3 ppm Maximum ($\pm 5\%$)
Frequency Stability vs. Load	± 0.2 ppm Maximum (± 2 pF)
Frequency Stability vs. Aging	± 1 ppm/Year Maximum (at 25°C)
Operating Temperature Range	0°C to +50°C
Supply Voltage	3.3Vdc $\pm 5\%$
Input Current	20mA Maximum
Output Voltage Logic High (Voh)	90% of Vdd Minimum
Output Voltage Logic Low (Vol)	10% of Vdd Maximum
Rise/Fall Time	10nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50 ± 10 (%) (Measured at 50% of waveform)
Load Drive Capability	15pF Maximum
Output Logic Type	CMOS
Control Voltage	None (No Connect on Pin 1)
Internal Trim	± 3 ppm Minimum (Top of Can)
Modulation Bandwidth	10kHz Minimum (Measured at -3dB with a Control Voltage of 1.65Vdc)
Input Impedance	10kOhms Typical
Phase Noise	-70dBc at 10Hz Offset -100dBc at 100Hz Offset -130dBc at 1kHz Offset -140dBc at 10kHz Offset -145dBc at 100kHz Offset (All Values are Typical)
Storage Temperature Range	-40°C to +85°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

Fine Leak Test	MIL-STD-883, Method 1014 Condition A (Internal Crystal Only)
Gross Leak Test	MIL-STD-883, Method 1014 Condition C (Internal Crystal Only)
Lead Integrity	MIL-STD-883, Method 2004
Mechanical Shock	MIL-STD-202, Method 213 Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010
Vibration	MIL-STD-883, Method 2007 Condition A

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MECHANICAL DIMENSIONS (all dimensions in millimeters)

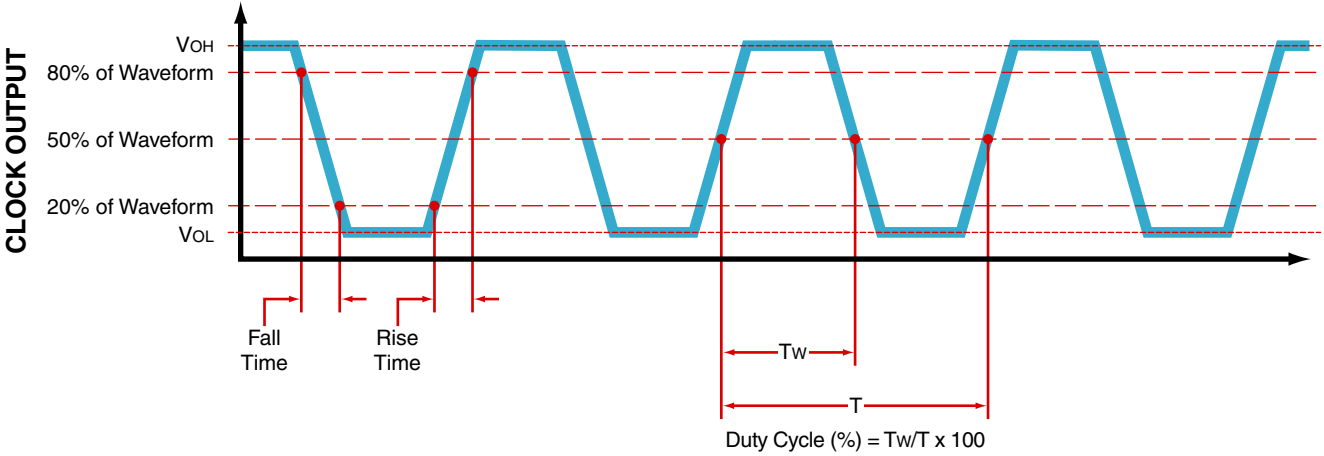


PIN	CONNECTION
1	No Connect
2	Case/Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	25.000M
3	XXXXXX XXXXX=Ecliptek Manufacturing Identifier

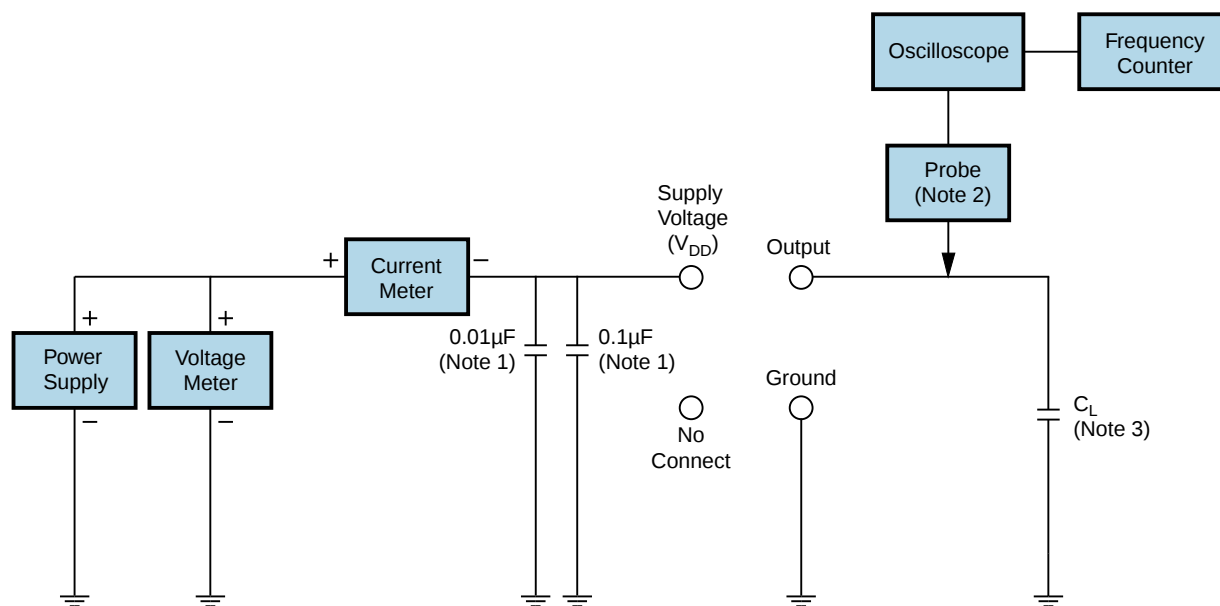
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OUTPUT WAVEFORM



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Test Circuit for No Connect Option



Note 1: An external 0.01 μ F ceramic bypass capacitor in parallel with a 0.1 μ F high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

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Recommended Solder Reflow Methods



Low Temperature Solder Bath (Wave Solder)

Ts MAX to Tl (Ramp-up Rate)	5°C/Second Maximum
Preheat	
- Temperature Minimum (Ts MIN)	N/A
- Temperature Typical (Ts TYP)	150°C
- Temperature Maximum (Ts MAX)	N/A
- Time (ts MIN)	30 - 60 Seconds
Ramp-up Rate (Tl to Tp)	5°C/Second Maximum
Time Maintained Above:	
- Temperature (Tl)	150°C
- Time (tL)	200 Seconds Maximum
Peak Temperature (Tp)	245°C Maximum
Target Peak Temperature (Tp Target)	245°C Maximum 1 Time / 235°C Maximum 2 Times
Time within 5°C of actual peak (tp)	5 Seconds Maximum 1 Time / 15 Seconds Maximum 2 Times
Ramp-down Rate	5°C/Second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1

Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum. (Temperatures listed are applied to device leads only.)

High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum. (Temperatures listed are applied to device leads only.)

Low Temperature Solder Bath (Wave Solder) Note 1

Device is non-hermetic; Post reflow aqueous wash is not recommended

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Low Temperature Solder Bath (Wave Solder) Note 2

Temperatures shown are applied to back of PCB board and device leads only.